

# 2N4125



# **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents of 10  $\mu A$  to 100 mA.

#### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	30	V	
V <sub>CBO</sub>	Collector-Base Voltage	30	V	
V <sub>EBO</sub>	Emitter-Base Voltage 4.0		V	
lc	Collector Current - Continuous	200	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N4125	
P <sub>D</sub>	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier (continued)

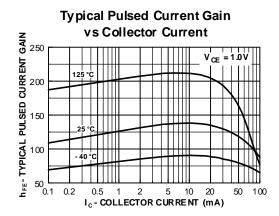
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	30		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4.0		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 20 \text{ V}, I_{E} = 0$		50	nA
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		50	nA
VCF(sat)	Collector-Emitter Saturation Voltage	$V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$ $I_{C} = 50 \text{ mA}. I_{B} = 5.0 \text{ mA}$	25	0.4	V
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	50	150	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.95	V
SMALL S	IGNAL CHARACTERISTICS Output Capacitance	V <sub>CB</sub> = 5.0 V, f = 100 kHz		4.5	pF
C <sub>ib</sub>	Input Capacitance	V <sub>BE</sub> = 0.5 V, f = 100 kHz		10	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0  kHz $I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100  MHz	50 2.0	200	
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \text{ μA},$ $R_{S} = 1.0 \text{ k}\Omega,$ $f = 10\text{Hz}$ to 15.7 kHz.		5.0	dB

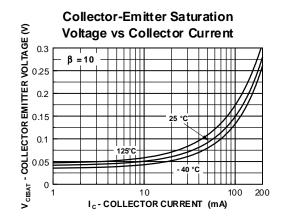
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

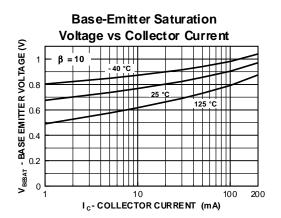
#### **PNP General Purpose Amplifier**

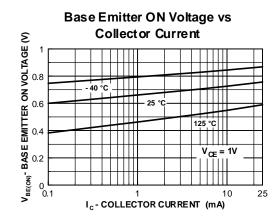
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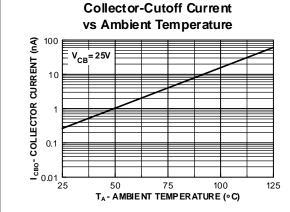
## **Typical Characteristics**

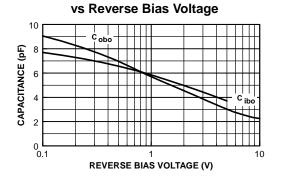












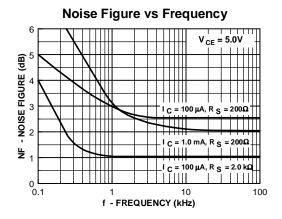
**Common-Base Open Circuit** 

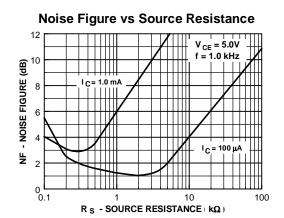
**Input and Output Capacitance** 

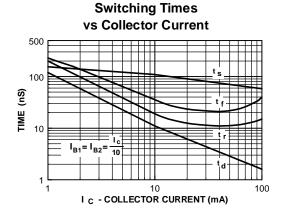
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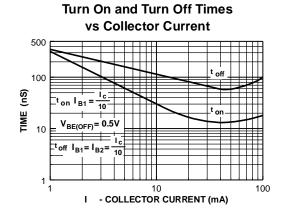
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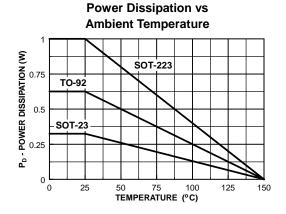
#### Typical Characteristics (continued)







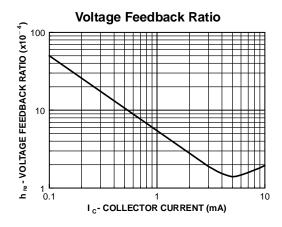


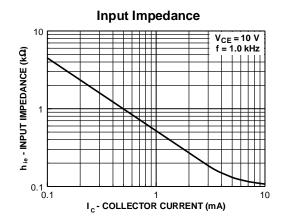


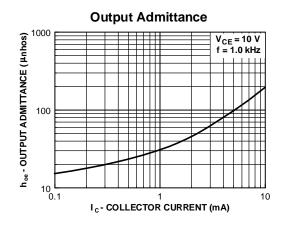
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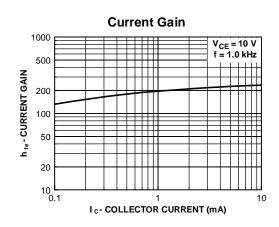
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## Typical Characteristics (continued)









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